

The documentation and process conversion measures necessary to comply with this document shall be completed by 26 July 2019.

INCH-POUND

MIL-PRF-19500/276K  
 27 March 2019  
 SUPERSEDING  
 MIL-PRF-19500/276J  
 28 November 2014

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, THYRISTORS (CONTROLLED RECTIFIERS), SILICON,  
 TYPES 2N2323, 2N2324, 2N2326, 2N2328, AND A VERSIONS,  
 THROUGH-HOLE AND SURFACE MOUNT PACKAGES,  
 QUALITY LEVELS JAN, JANTX, AND JANTXV

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for PNP, silicon, reverse-blocking-triode thyristors. Three levels of product assurance (JAN, JANTX, and JANTXV) are provided for each device type as specified in [MIL-PRF-19500](#).

1.2 Package outline. The device package outlines are a TO-205AA or TO-205AD (formerly TO-5, TO-39) in accordance with [figure 1](#) and a 3 terminal SMD package (U4) in accordance with [figure 2](#).

1.3 Maximum ratings.

Type	V <sub>RM</sub>	V <sub>RM</sub> (non-rep)	V <sub>FBXM</sub>	I <sub>o</sub> (1)	I <sub>FSM</sub> (2)	V <sub>GKM</sub>	T <sub>STG</sub> , T <sub>J</sub>	R <sub>θJA</sub> max	R <sub>θJC</sub> max	R <sub>θJSP</sub> max	Barometric pressure
	V (pk)	V (pk)	V (pk)	A dc	A(pk)	V (pk)	°C	°C/W	°C/W	°C/W	mm Hg
2N2323, S, U4	50	75	50 (3)	.22	15	6	-65	175	15	6	
2N2323A, AS, AU4	50	75	50 (4)	.22	15	6	to				
2N2324, S, U4	100	150	100 (3)	.22	15	6	+150				
2N2324A, AS, AU4	100	150	100 (4)	.22	15	6					
2N2326, S, U4	200	300	200 (3)	.22	15	6					
2N2326A, AS, AU4	200	300	200 (4)	.22	15	6					
2N2328, S, U4	300	400	300 (3)	.22	15	6					15
2N2328A, AS, AU4	300	400	300 (4)	.22	15	6					15
2N2329, S, U4	400	500	400 (3)	.22	15	6					15
2N2329A, AS, AU4	400	500	400 (4)	.22	15	6					15

- (1) This average forward current is for an ambient temperature of 80°C and 180 electrical degrees of conduction. For other operating conditions see [figure 3](#).
- (2) Surge current is non-recurrent. The rate of rise of peak surge current shall not exceed 40 A during the first 5 μs after switching from the "off" (blocking) to the "on" (conducting) state. This is measured from the point where the thyristor voltage has decayed to 90 percent of its initial blocking value.
- (3) Gate connected to cathode through 1,000 ohm resistor.
- (4) Gate connected to cathode through 2,000 ohm resistor.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to [Semiconductor@dla.mil](mailto:Semiconductor@dla.mil). Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.

AMSC N/A

